

Min-Kyu Joo

List of Publications by Year in descending order

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times ranked

1826
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|------|-----------|
| 1 | Hidden surface channel in two-dimensional multilayers. <i>2D Materials</i> , 2022, 9, 035004. | 4.4 | 5 |
| 2 | Emergence of Quantum Tunneling in Ambipolar Black Phosphorus Multilayers without Heterojunctions. <i>Advanced Functional Materials</i> , 2022, 32, . | 14.9 | 6 |
| 3 | Understanding random telegraph noise in two-dimensional BP/ReS ₂ heterointerface. <i>Applied Physics Letters</i> , 2022, 120, 253507. | 3.3 | 3 |
| 4 | Defect spectroscopy of sidewall interfaces in gate-all-around silicon nanosheet FET. <i>Nanotechnology</i> , 2021, 32, 165202. | 2.6 | 3 |
| 5 | Metal-Contact Improvement in a Multilayer WSe ₂ Transistor through Strong Hot Carrier Injection. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 2829-2835. | 8.0 | 3 |
| 6 | Restricted Channel Migration in 2D Multilayer ReS ₂ . <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 19016-19022. | 8.0 | 13 |
| 7 | Degradation pattern of contact resistance and characteristic trap energy in blue organic light-emitting diodes. <i>Organic Electronics</i> , 2021, 91, 106067. | 2.6 | 4 |
| 8 | Multiple machine learning approach to characterize two-dimensional nanoelectronic devices via featurization of charge fluctuation. <i>Npj 2D Materials and Applications</i> , 2021, 5, . | 7.9 | 7 |
| 9 | Effect of interlayer tunneling barrier on carrier transport and fluctuation in multilayer ReS ₂ . <i>Applied Physics Letters</i> , 2020, 117, . | 3.3 | 6 |
| 10 | Coulomb drag transistor using a graphene and MoS ₂ heterostructure. <i>Communications Physics</i> , 2020, 3, . | 5.3 | 11 |
| 11 | High-mobility junction field-effect transistor via graphene/MoS ₂ heterointerface. <i>Scientific Reports</i> , 2020, 10, 13101. | 3.3 | 32 |
| 12 | Origin of relaxation frequency shift in blue organic light-emitting diodes. <i>Applied Physics Letters</i> , 2020, 117, 103301. | 3.3 | 3 |
| 13 | Origin of exciplex degradation in organic light emitting diodes: Thermal stress effects over glass transition temperature of emission layer. <i>Applied Physics Letters</i> , 2020, 117, . | 3.3 | 12 |
| 14 | Understanding tunable photoresponsivity of two-dimensional multilayer phototransistors: Interplay between thickness and carrier mobility. <i>Applied Physics Letters</i> , 2020, 116, . | 3.3 | 14 |
| 15 | Drain induced barrier increasing in multilayer ReS ₂ . <i>2D Materials</i> , 2020, 7, 031004. | 4.4 | 13 |
| 16 | Temperature-Dependent Opacity of the Gate Field Inside MoS ₂ Field-Effect Transistors. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 29022-29028. | 8.0 | 7 |
| 17 | Impact of Heat Treatment on a Hetero-Stacked MoS ₂ /h-BN Field-Effect Transistor. <i>IEEE Electron Device Letters</i> , 2019, 40, 1626-1629. | 3.9 | 1 |
| 18 | Low-Voltage-Operated Highly Sensitive Graphene Hall Elements by Ionic Gating. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 4226-4232. | 8.0 | 3 |

| # | ARTICLE | IF | CITATIONS |
|----|--|------|-----------|
| 19 | Room-Temperature Mesoscopic Fluctuations and Coulomb Drag in Multilayer WSe ₂ . Advanced Materials, 2019, 31, e1900154. | 21.0 | 12 |
| 20 | Coulomb scattering mechanism transition in 2D layered MoTe ₂ : effect of high- <i>I_p</i> passivation and Schottky barrier height. Nanotechnology, 2019, 30, 035206. | 2.6 | 7 |
| 21 | Hydrothermal Synthesis of Stable 1T-WSe ₂ and Single-Walled Carbon Nanotube Hybrid Flexible Thin Films with Enhanced Thermoelectric Performance. Energy Technology, 2018, 6, 1921-1928. | 3.8 | 18 |
| 22 | Near-zero hysteresis and near-ideal subthreshold swing in h-BN encapsulated single-layer MoS ₂ field-effect transistors. 2D Materials, 2018, 5, 031001. | 4.4 | 104 |
| 23 | Probing Distinctive Electron Conduction in Multilayer Rhenium Disulfide. Advanced Materials, 2018, 31, 1805860. | 21.0 | 16 |
| 24 | Electrothermal Local Annealing via Graphite Joule Heating on Two-Dimensional Layered Transistors. ACS Applied Materials & Interfaces, 2018, 10, 25638-25643. | 8.0 | 3 |
| 25 | Understanding Coulomb Scattering Mechanism in Monolayer MoS ₂ Channel in the Presence of <i>h</i> -BN Buffer Layer. ACS Applied Materials & Interfaces, 2017, 9, 5006-5013. | 8.0 | 37 |
| 26 | Junction-Structure-Dependent Schottky Barrier Inhomogeneity and Device Ideality of Monolayer MoS ₂ Field-Effect Transistors. ACS Applied Materials & Interfaces, 2017, 9, 11240-11246. | 8.0 | 57 |
| 27 | Degradation pattern of black phosphorus multilayer field-effect transistors in ambient conditions: Strategy for contact resistance engineering in BP transistors. Applied Surface Science, 2017, 419, 637-641. | 6.1 | 12 |
| 28 | Thickness-dependent carrier mobility of ambipolar MoTe ₂ : Interplay between interface trap and Coulomb scattering. Applied Physics Letters, 2017, 110, . | 3.3 | 42 |
| 29 | Tunable Mobility in Double-Gated MoTe ₂ Field-Effect Transistor: Effect of Coulomb Screening and Trap Sites. ACS Applied Materials & Interfaces, 2017, 9, 29185-29192. | 8.0 | 31 |
| 30 | Probing defect dynamics in monolayer MoS ₂ via noise nanospectroscopy. Nature Communications, 2017, 8, 2121. | 12.8 | 56 |
| 31 | Suppression of Interfacial Current Fluctuation in MoTe ₂ Transistors with Different Dielectrics. ACS Applied Materials & Interfaces, 2016, 8, 19092-19099. | 8.0 | 35 |
| 32 | Strong Coulomb scattering effects on low frequency noise in monolayer WS ₂ field-effect transistors. Applied Physics Letters, 2016, 109, . | 3.3 | 18 |
| 33 | Electron Excess Doping and Effective Schottky Barrier Reduction on the MoS ₂ / <i>h</i> -BN Heterostructure. Nano Letters, 2016, 16, 6383-6389. | 9.1 | 78 |
| 34 | Surface Modulation of Graphene Field Effect Transistors on Periodic Trench Structure. ACS Applied Materials & Interfaces, 2016, 8, 18513-18518. | 8.0 | 3 |
| 35 | Evaluation of power generated by thermoelectric modules comprising a p-type and n-type single walled carbon nanotube composite paper. RSC Advances, 2015, 5, 78099-78103. | 3.6 | 17 |
| 36 | Plasma treatment effect on charge carrier concentrations and surface traps in a-InGaZnO thin-film transistors. Journal of Applied Physics, 2014, 115, . | 2.5 | 46 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 37 | Effect of Intertube Junctions on the Thermoelectric Power of Monodispersed Single Walled Carbon Nanotube Networks. Journal of Physical Chemistry C, 2014, 118, 26454-26461. | 3.1 | 43 |
| 38 | Nitrogen-plasma treatment of parallel-aligned SnO ₂ -nanowire field-effect transistors. Journal of the Korean Physical Society, 2014, 65, 502-508. | 0.7 | 1 |
| 39 | Separation of interlayer resistance in multilayer MoS ₂ field-effect transistors. Applied Physics Letters, 2014, 104, . | 3.3 | 46 |
| 40 | Low-frequency noise in multilayer MoS ₂ field-effect transistors: the effect of high-k passivation. Nanoscale, 2014, 6, 433-441. | 5.6 | 146 |
| 41 | Reduced charge fluctuations in individual SnO ₂ nanowires by suppressed surface reactions. Journal of Materials Chemistry, 2012, 22, 24012. | 6.7 | 22 |
| 42 | A dual analyzer for real-time impedance and noise spectroscopy of nanoscale devices. Review of Scientific Instruments, 2011, 82, 034702. | 1.3 | 26 |
| 43 | Controlled surface adsorption of fd filamentous phage by tuning of the pH and the functionalization of the surface. Journal of Applied Physics, 2011, 109, 064701. | 2.5 | 11 |